

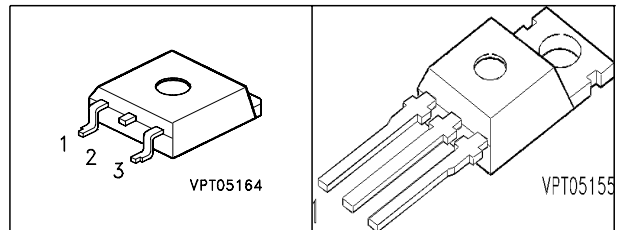
OptiMOS™ Power-Transistor

Features

- N-Channel
- Enhancement mode
- Avalanche rated
- Logic Level
- dv/dt rated
- 175°C operating temperature

Product Summary

Drain source voltage	V_{DS}	55	V
Drain-source on-state resistance	$R_{DS(on)}$	7	mΩ
Continuous drain current	I_D	80	A



Type	Package	Ordering Code	Marking	Pin 1	PIN 2/4	PIN 3
SPP80N06S2L-07	P-TO220-3-1	Q67040-S4285	2N06L07	G	D	S
SPB80N06S2L-07	P-TO263-3-2	Q67040-S4288	2N06L07			

Maximum Ratings, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current $T_C = 25\text{ °C}$, F) $T_C = 100\text{ °C}$	I_D	80 80	A
Pulsed drain current $T_C = 25\text{ °C}$	$I_{D\text{ puls}}$	320	
Avalanche energy, single pulse $I_D = 80\text{ A}$, $V_{DD} = 25\text{ V}$, $R_{GS} = 25\text{ Ω}$	E_{AS}	450	mJ
Reverse diode dv/dt $I_S = 80\text{ A}$, $V_{DS} = 44\text{ V}$, $di/dt = 200\text{ A/μs}$, $T_{jmax} = 175\text{ °C}$	dv/dt	6	kV/μs
Gate source voltage	V_{GS}	±20	V
Power dissipation $T_C = 25\text{ °C}$	P_{tot}	210	W
Operating and storage temperature	T_j, T_{stg}	-55...+175	°C
IEC climatic category; DIN IEC 68-1		55/175/56	

¹current limited by bondwire; with an $R_{thJC} = 0.7\text{ K/W}$ the chip is able to carry $I_D = 122\text{ A}$.

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - case	R_{thJC}	-	-	0.7	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	62	
SMD version, device on PCB: @ min. footprint @ 6 cm ² cooling area ^{F)}	R_{thJA}	-	-	62 40	

Electrical Characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain-source breakdown voltage $V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	$V_{(BR)DSS}$	55	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D = 150\text{ }\mu\text{A}$	$V_{GS(th)}$	1.2	1.6	2	
Zero gate voltage drain current $V_{DS} = 55\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = 25\text{ }^\circ\text{C}$ $V_{DS} = 55\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = 125\text{ }^\circ\text{C}$	I_{DSS}	-	0.01 1	1 100	μA
Gate-source leakage current $V_{GS} = 20\text{ V}$, $V_{DS} = 0\text{ V}$	I_{GSS}	-	1	100	
Drain-source on-state resistance $V_{GS} = 4.5\text{ V}$, $I_D = 60\text{ A}$	$R_{DS(on)}$	-	6.7	10	m Ω
Drain-source on-state resistance $V_{GS} = 10\text{ V}$, $I_D = 60\text{ A}$	$R_{DS(on)}$	-	5.3	7	

¹Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic Characteristics

Transconductance	g_{fs}	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 80\text{A}$	52	104	-	S
Input capacitance	C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$	-	3160	4000	pF
Output capacitance	C_{oss}		-	780	1000	
Reverse transfer capacitance	C_{rss}		-	215	290	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 30\text{V}$, $V_{GS} = 4.5\text{V}$, $I_D = 80\text{A}$, $R_G = 2\Omega$	-	18	27	ns
Rise time	t_r		-	350	520	
Turn-off delay time	$t_{d(off)}$		-	28	42	
Fall time	t_f		-	31	47	

Gate Charge Characteristics

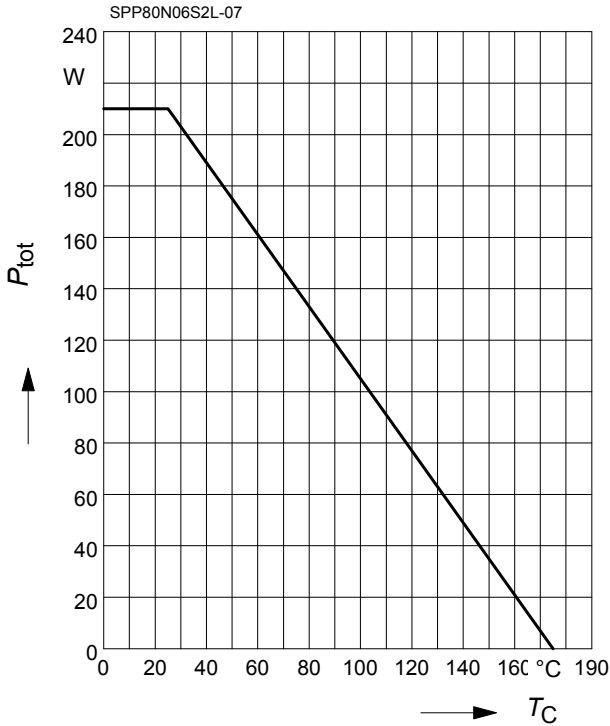
Gate to source charge	Q_{gs}	$V_{DD} = 44\text{V}$, $I_D = 80\text{A}$	-	11	15	nC
Gate to drain charge	Q_{gd}		-	32	40	
Gate charge total	Q_g	$V_{DD} = 44\text{V}$, $I_D = 80\text{A}$, $V_{GS} = 0$ to 10V	-	97	120	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 44\text{V}$, $I_D = 80\text{A}$	-	3.5	-	V

Reverse Diode

Inverse diode continuous forward current	I_S	$T_C = 25\text{ }^\circ\text{C}$	-	-	80	A
Inverse diode direct current, pulsed	I_{SM}		-	-	320	
Inverse diode forward voltage	V_{SD}	$V_{GS} = 0\text{V}$, $I_F = 80\text{A}$	-	0.9	1.3	V
Reverse recovery time	t_{rr}	$V_R = 30\text{V}$, $I_F = I_S$, $di_F/dt = 100\text{A}/\mu\text{s}$	-	50	62	ns
Reverse recovery charge	Q_{rr}		-	105	130	nC

1 Power dissipation

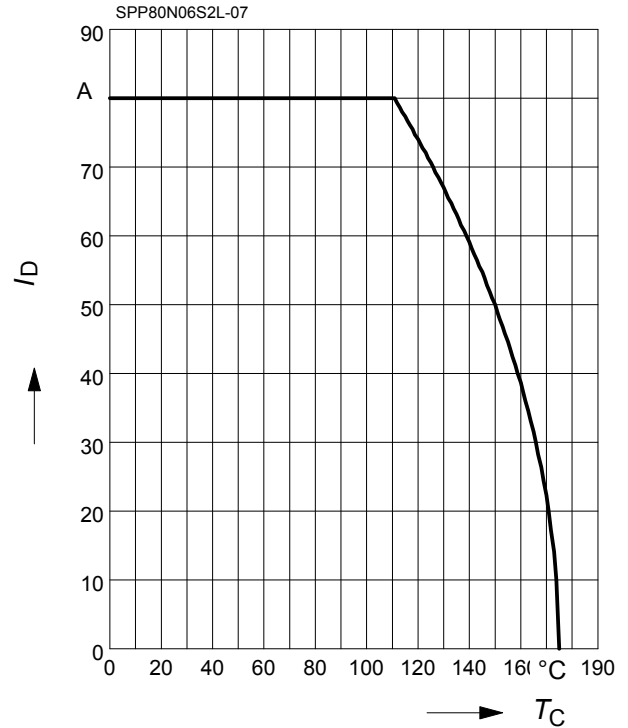
$$P_{tot} = f(T_C)$$



2 Drain current

$$I_D = f(T_C)$$

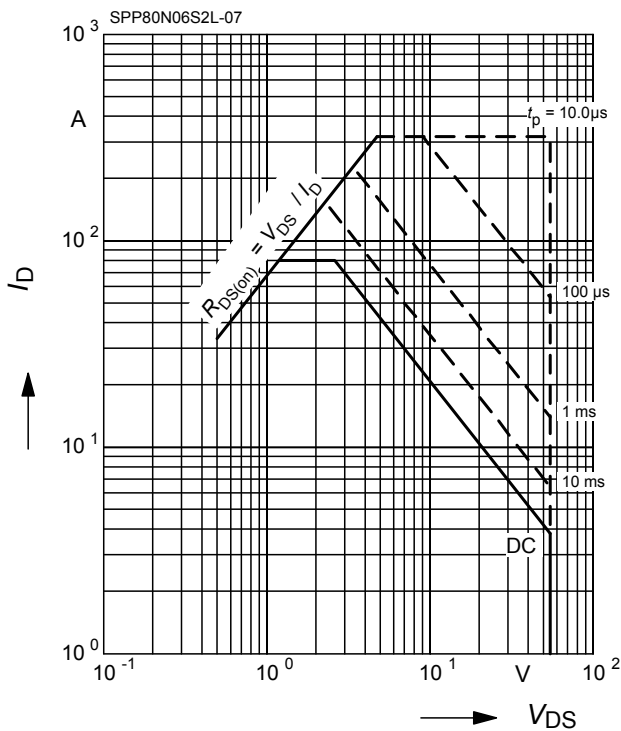
parameter: $V_{GS} \geq 10 \text{ V}$



Safe operating area

$$I_D = f(V_{DS})$$

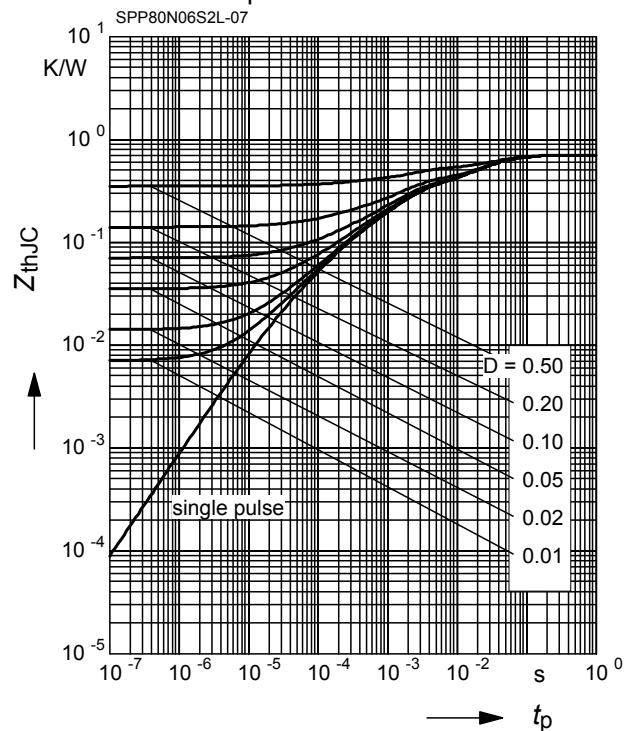
parameter: $D = 0, T_C = 25 \text{ °C}$



4 Transient thermal impedance

$$Z_{thJC} = f(t_p)$$

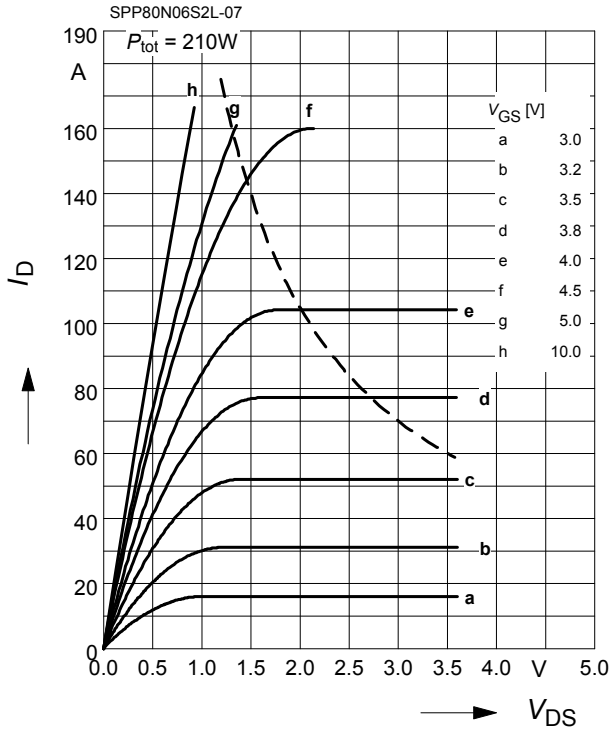
parameter: $D = t_p/T$



5 Typ. output characteristic

$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$

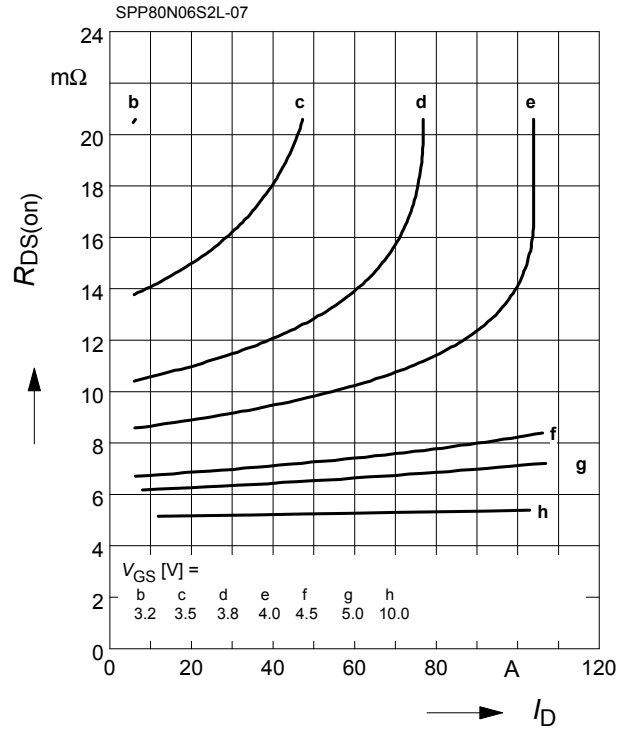
parameter: $t_p = 80 \mu\text{s}$



6 Typ. drain-source on resistance

$R_{DS(on)} = f(I_D)$

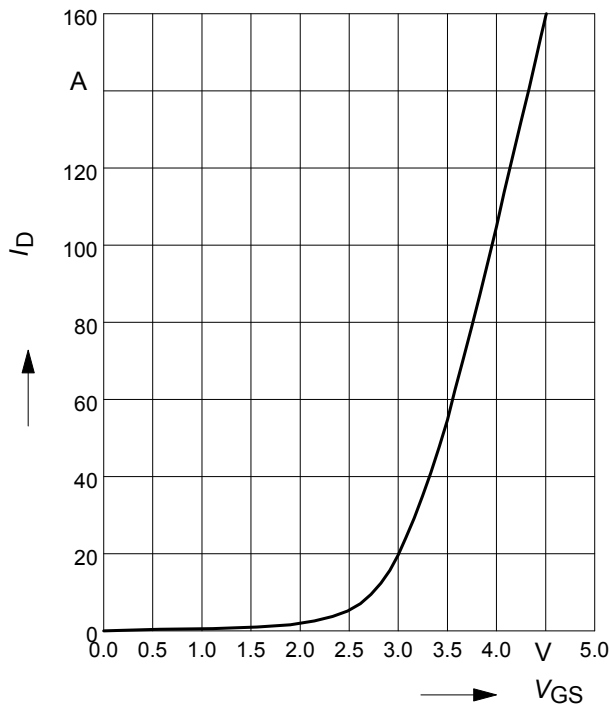
parameter: V_{GS}



7 Typ. transfer characteristics

$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$

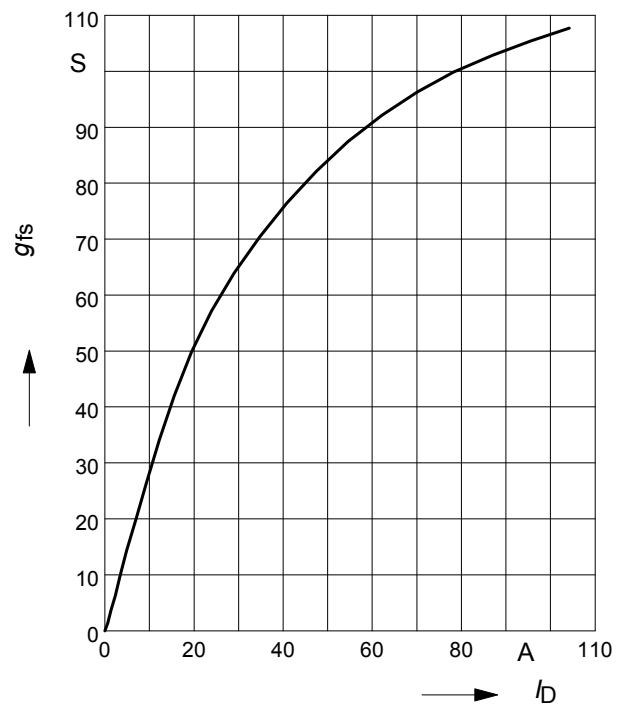
parameter: $t_p = 80 \mu\text{s}$



8 Typ. forward transconductance

$g_{fs} = f(I_D); T_j = 25^\circ\text{C}$

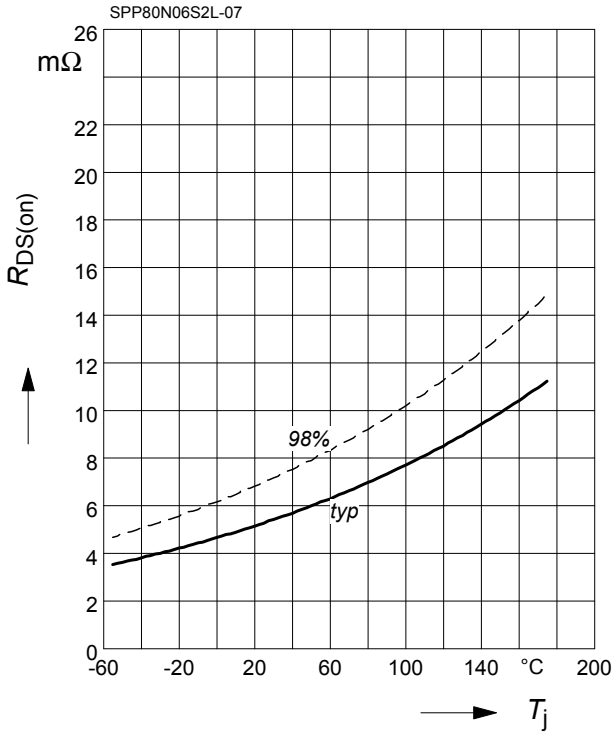
parameter: g_{fs}



9 Drain-source on-state resistance

$$R_{DS(on)} = f(T_j)$$

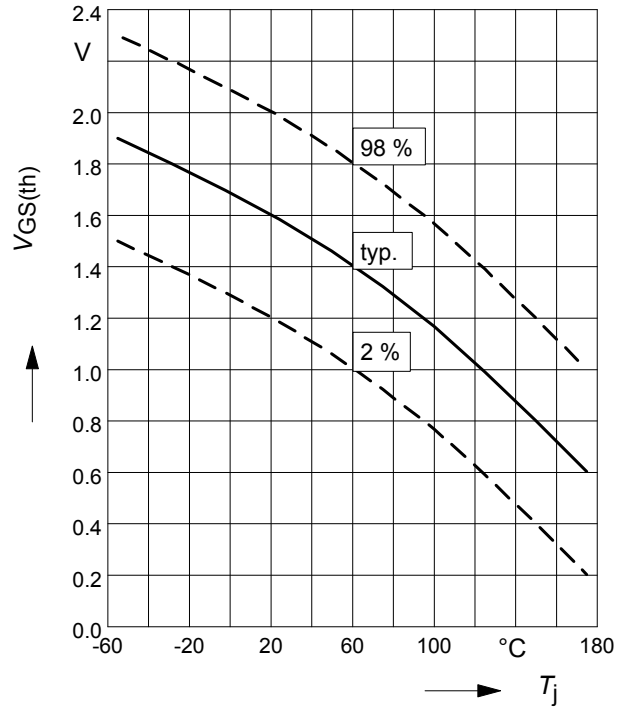
parameter: $I_D = 60\text{ A}$, $V_{GS} = 10\text{ V}$



Gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

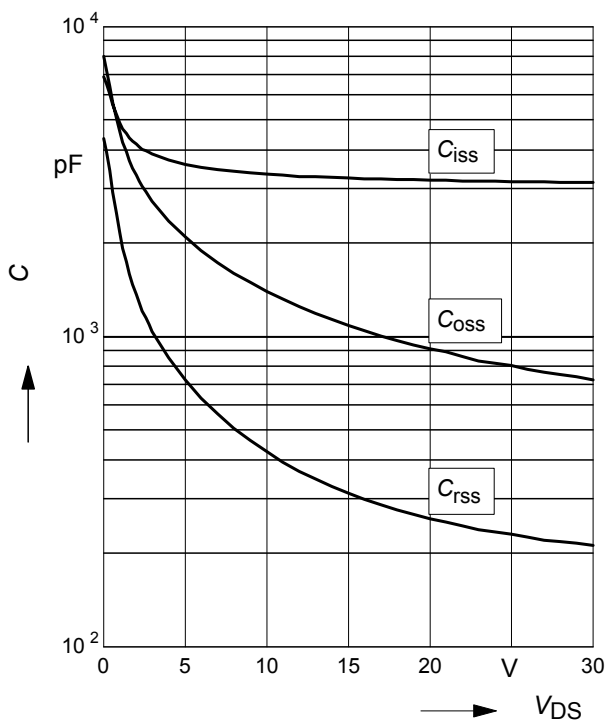
parameter: $V_{GS} = V_{DS}$, $I_D = 150\ \mu\text{A}$



11 Typ. capacitances

$$C = f(V_{DS})$$

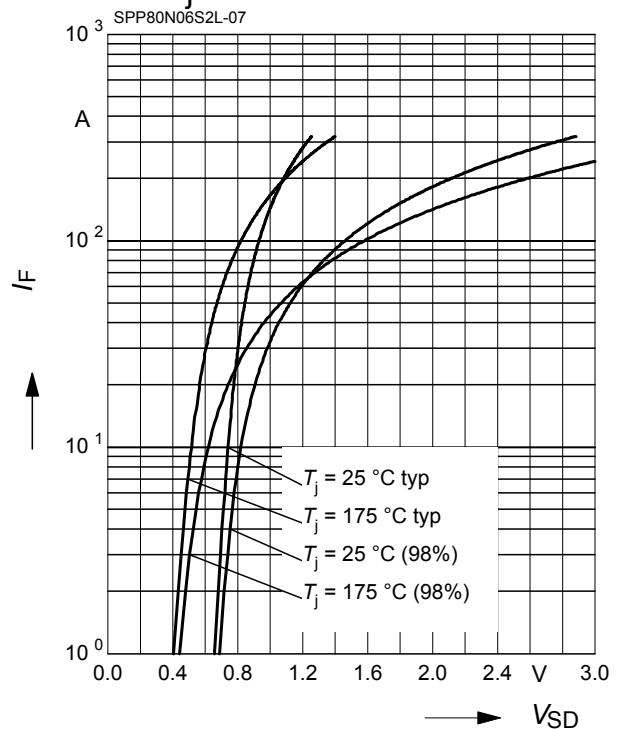
parameter: $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$



12 Forward character. of reverse diode

$$I_F = f(V_{SD})$$

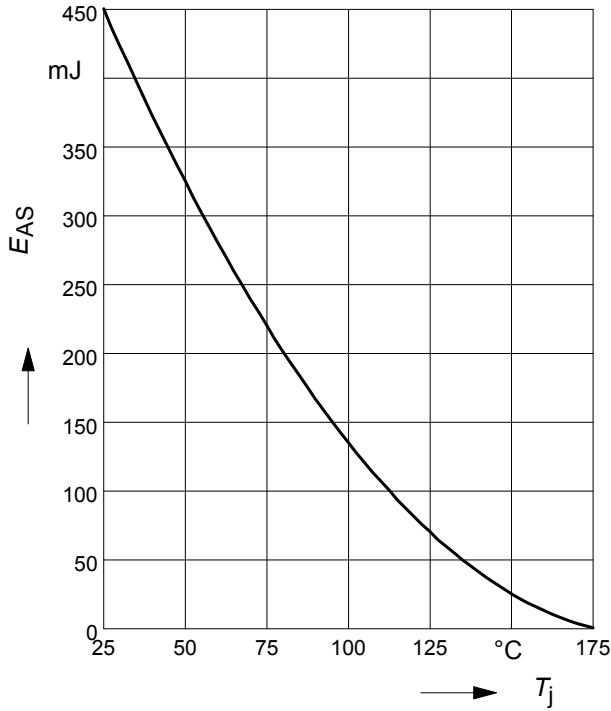
parameter: T_j , $t_p = 80\ \mu\text{s}$



13 Avalanche energy

$$E_{AS} = f(T_j)$$

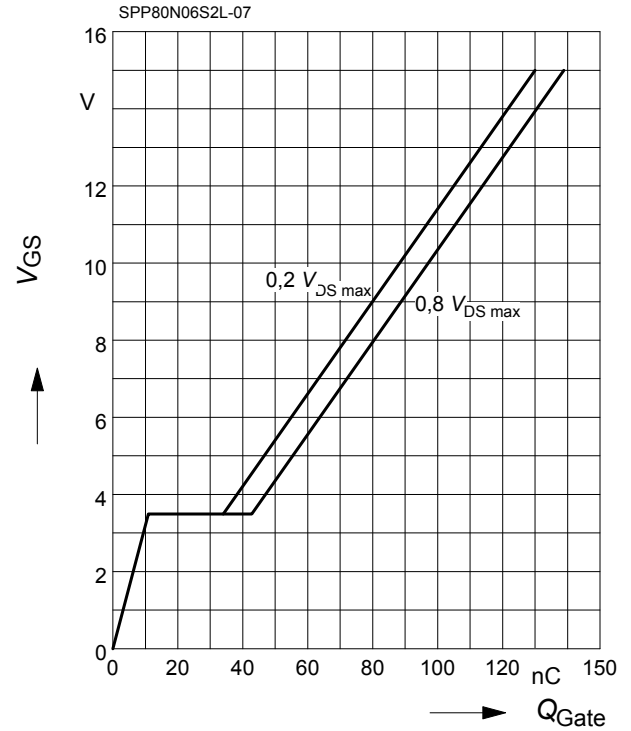
par.: $I_D = 80\text{ A}$, $V_{DD} = 25\text{ V}$, $R_{GS} = 25\ \Omega$



14 Typ. gate charge

$$V_{GS} = f(Q_{Gate})$$

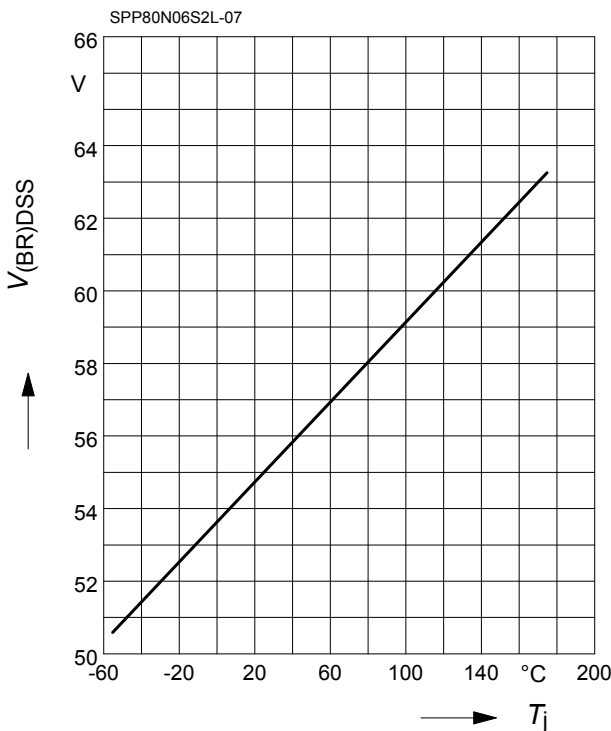
parameter: $I_D = 80\text{ A}$ pulsed



15 Drain-source breakdown voltage

$$V_{(BR)DSS} = f(T_j)$$

parameter: $I_D = 10\text{ mA}$



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